PEMB13; **PUMB13**

PNP/PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 47 k Ω

Rev. 4 — 7 December 2011

Product data sheet

1. Product profile

1.1 General description

PNP/PNP double Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

| Type number | | | | NPN/NPN | Package |
|-------------|--------|-------|------------|------------|---------------------------|
| | NXP | JEITA | complement | complement | configuration |
| PEMB13 | SOT666 | - | PEMD13 | PEMH13 | ultra small and flat lead |
| PUMB13 | SOT363 | SC-88 | PUMD13 | PUMH13 | very small |

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

1.4 Quick reference data

Table 2. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------|---------------------------|------------|-----|-----|------|------|
| Per transisto | or | | | | | |
| V_{CEO} | collector-emitter voltage | open base | - | - | -50 | V |
| Io | output current | | - | - | -100 | mA |
| R1 | bias resistor 1 (input) | | 3.3 | 4.7 | 6.1 | kΩ |
| R2/R1 | bias resistor ratio | | 8 | 10 | 12 | |



2. Pinning information

Table 3. Pinning

| Pin | Description | Simplified outline | Graphic symbol |
|-----|------------------------|--------------------|----------------|
| 1 | GND (emitter) TR1 | · | . , |
| 2 | input (base) TR1 | 6 5 4 | 6 5 4 |
| 3 | output (collector) TR2 | | |
| 4 | GND (emitter) TR2 | | R1 R2 |
| 5 | input (base) TR2 | | TR1 |
| 6 | output (collector) TR1 | 001aab555 | R2 R1 |
| | | | 1 2 3 |
| | | | 006aaa21 |

3. Ordering information

Table 4. Ordering information

| Type number | Package | ackage | | | |
|-------------|---------|--|---------|--|--|
| | Name | Description | Version | | |
| PEMB13 | - | plastic surface-mounted package; 6 leads | SOT666 | | |
| PUMB13 | SC-88 | plastic surface-mounted package; 6 leads | SOT363 | | |

4. Marking

Table 5. Marking codes

| Type number | Marking code ^[1] |
|-------------|-----------------------------|
| PEMB13 | 45 |
| PUMB13 | B*5 |

[1] * = placeholder for manufacturing site code

5. Limiting values

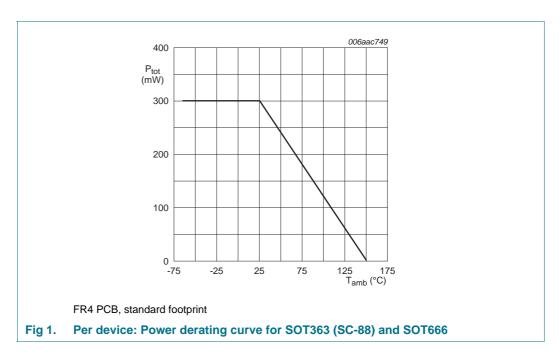
Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|---------------------------|--------------------------------------|--------------|------|------|
| Per transis | stor | | | | |
| V_{CBO} | collector-base voltage | open emitter | - | -50 | V |
| V_{CEO} | collector-emitter voltage | open base | - | -50 | V |
| V_{EBO} | emitter-base voltage | open collector | - | -5 | V |
| V_{I} | input voltage | | | | |
| | positive | | - | +5 | V |
| | negative | | - | -30 | V |
| Io | output current | | - | -100 | mA |
| I _{CM} | peak collector current | single pulse; $t_p \le 1 \text{ ms}$ | - | -100 | mA |
| P _{tot} | total power dissipation | $T_{amb} \le 25 ^{\circ}C$ | | | |
| | PEMB13 (SOT666) | | [1][2] | 200 | mW |
| | PUMB13 (SOT363) | | <u>[1]</u> _ | 200 | mW |
| Per device |) | | | | |
| P _{tot} | total power dissipation | $T_{amb} \le 25 ^{\circ}C$ | | | |
| | PEMB13 (SOT666) | | [1][2] - | 300 | mW |
| | PUMB13 (SOT363) | | <u>[1]</u> _ | 300 | mW |
| Tj | junction temperature | | - | 150 | °C |
| T _{amb} | ambient temperature | | -65 | +150 | °C |
| T _{stg} | storage temperature | | -65 | +150 | °C |

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.



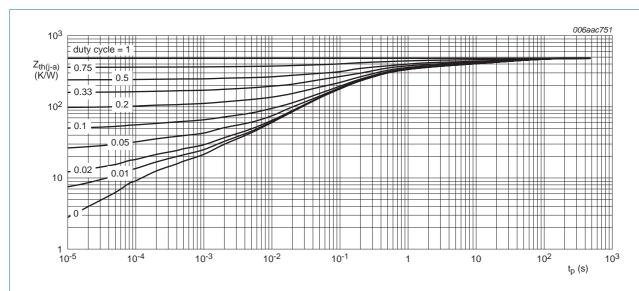
6. Thermal characteristics

Table 7. Thermal characteristics

| Parameter | Conditions | Min | Тур | Max | Unit |
|---|---|---|--|--|---|
| Per transistor | | | | | |
| thermal resistance from junction to ambient | in free air | | | | |
| PEMB13 (SOT666) | | [1][2] | - | 625 | K/W |
| PUMB13 (SOT363) | | <u>[1]</u> _ | - | 625 | K/W |
| | | | | | |
| thermal resistance from junction to ambient | in free air | | | | |
| PEMB13 (SOT666) | | [1][2] _ | - | 417 | K/W |
| PUMB13 (SOT363) | | <u>[1]</u> - | - | 417 | K/W |
| | thermal resistance from junction to ambient PEMB13 (SOT666) PUMB13 (SOT363) thermal resistance from junction to ambient PEMB13 (SOT666) | thermal resistance from in free air junction to ambient PEMB13 (SOT666) PUMB13 (SOT363) thermal resistance from in free air junction to ambient PEMB13 (SOT666) | thermal resistance from in free air junction to ambient PEMB13 (SOT666) PUMB13 (SOT363) 11 - thermal resistance from in free air junction to ambient PEMB13 (SOT666) 11 2 - | thermal resistance from in free air junction to ambient PEMB13 (SOT666) PUMB13 (SOT363) [1] thermal resistance from in free air junction to ambient PEMB13 (SOT666) [1][2] | thermal resistance from junction to ambient PEMB13 (SOT666) PUMB13 (SOT363) Ill 625 thermal resistance from junction to ambient PEMB13 (SOT666) Ill 417 |

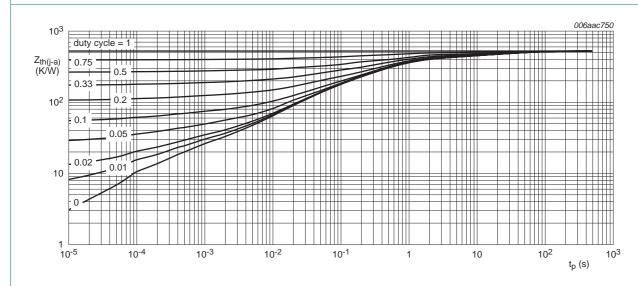
^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.



FR4 PCB, standard footprint

Fig 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration for PEMB13 (SOT666); typical values



FR4 PCB, standard footprint

Fig 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration for PUMB13 (SOT363); typical values

PNP/PNP resistor-equipped transistors; R1 = 4.7 kΩ, R2 = 47 kΩ

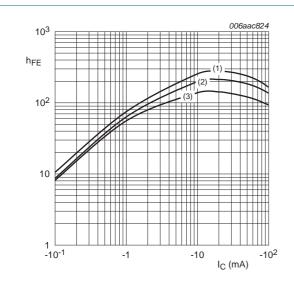
7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--------------------|--------------------------------------|--|------|------|------|------|
| Per trans | istor | | | | | |
| I _{CBO} | collector-base cut-off current | $V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$ | - | - | -100 | nA |
| I _{CEO} | collector-emitter cut-off | $V_{CE} = -30 \text{ V}; I_B = 0 \text{ A}$ | - | - | -1 | μΑ |
| | current | $V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$ | - | - | -5 | μΑ |
| I _{EBO} | emitter-base cut-off current | $V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$ | - | - | -170 | μΑ |
| h _{FE} | DC current gain | $V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA}$ | 100 | - | - | |
| V _{CEsat} | collector-emitter saturation voltage | $I_C = -5 \text{ mA}; I_B = -0.25 \text{ mA}$ | - | - | -100 | mV |
| $V_{I(off)}$ | off-state input voltage | $V_{CE} = -5 \text{ V}; I_{C} = -100 \mu\text{A}$ | - | -0.6 | -0.5 | V |
| V _{I(on)} | on-state input voltage | $V_{CE} = -0.3 \text{ V}; I_{C} = -5 \text{ mA}$ | -1.3 | -0.9 | - | V |
| R1 | bias resistor 1 (input) | | 3.3 | 4.7 | 6.1 | kΩ |
| R2/R1 | bias resistor ratio | | 8 | 10 | 12 | |
| C _c | collector capacitance | $V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz | - | - | 3 | pF |
| f _T | transition frequency | $V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA}; $ [1] f = 100 MHz | - | 180 | - | MHz |

^[1] Characteristics of built-in transistor



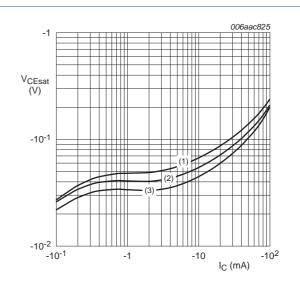
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 4. DC current gain as a function of collector current; typical values



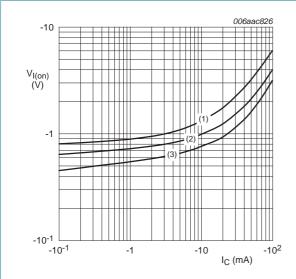
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 5. Collector-emitter saturation voltage as a function of collector current; typical values



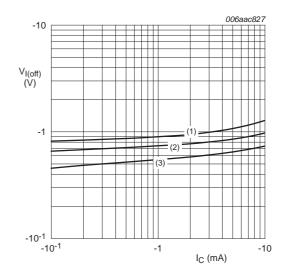
$$V_{CE} = -0.3 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 6. On-state input voltage as a function of collector current; typical values



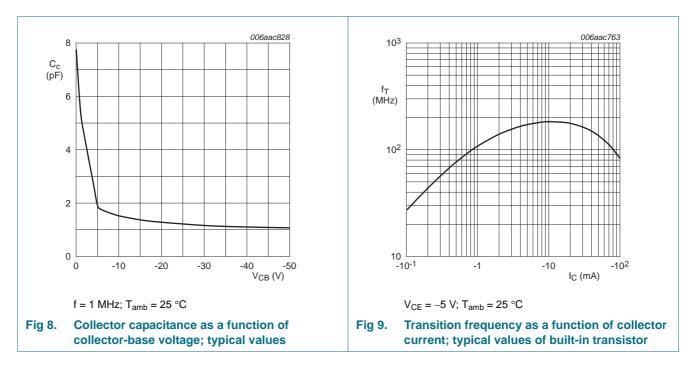
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 7. Off-state input voltage as a function of collector current; typical values

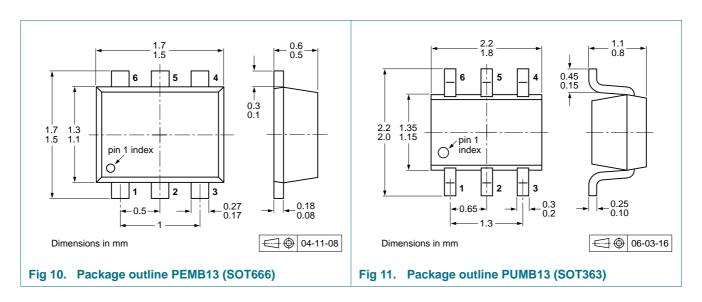


8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



PEMB13_PUMB13

10. Packing information

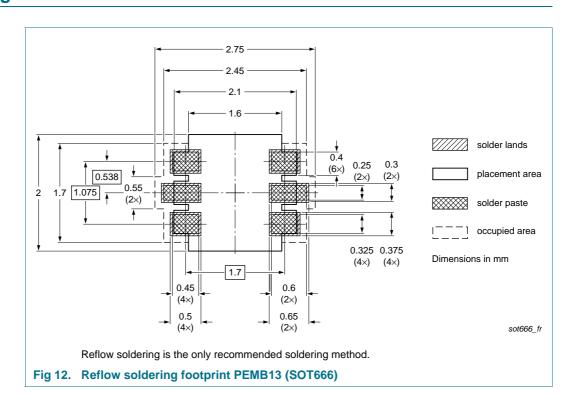
Table 9. Packing methods

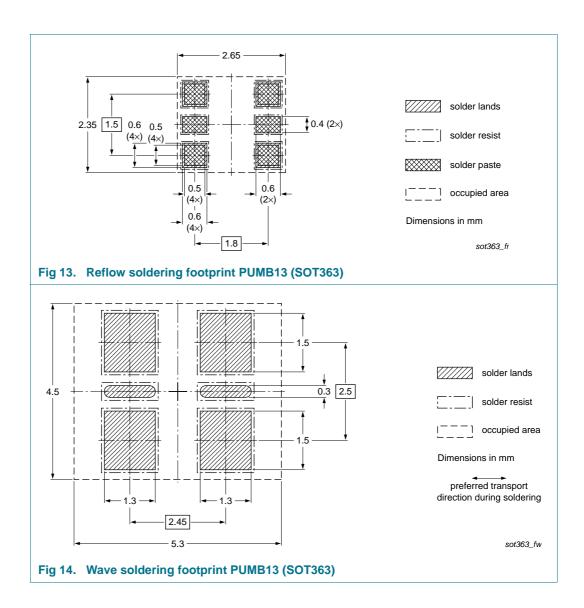
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

| Туре | Package | Description | Packir | Packing quantity | | | |
|---------------|---------|------------------------------------|--------|------------------|------|-------|--|
| number | | | | 4000 | 8000 | 10000 | |
| PEMB13 | SOT666 | 2 mm pitch, 8 mm tape and reel | - | - | -315 | - | |
| | | 4 mm pitch, 8 mm tape and reel | - | -115 | - | - | |
| PUMB13 SOT363 | | 4 mm pitch, 8 mm tape and reel; T1 | -115 | - | - | -135 | |
| | | 4 mm pitch, 8 mm tape and reel; T2 | -125 | - | - | -165 | |

- [1] For further information and the availability of packing methods, see Section 14.
- [2] T1: normal taping
- [3] T2: reverse taping

11. Soldering





PNP/PNP resistor-equipped transistors; R1 = 4.7 kΩ, R2 = 47 kΩ

12. Revision history

Table 10. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes | |
|-------------------|--|---|------------------------|---|--|
| PEMB13_PUMB13 v.4 | 20111207 | Product data sheet | - | PEMB13_PUMB13 v.3 | |
| Modifications: | | of this document has been f NXP Semiconductors. | redesigned to comply w | th the new identity | |
| | Legal texts have been adapted to the new company name where appropriate. | | | | |
| | Section 1 "Product profile": updated | | | | |
| | Section 4 "M | Marking": updated | | | |
| | • Figure 1 to 9: added | | | | |
| | Section 5 "Limiting values": updated | | | | |
| | Section 6 "Thermal characteristics": updated | | | | |
| | | aracteristics": V _{i(on)} redefine te input voltage, I _{CEO} updat | | t voltage, V _{i(off)} redefined to | |
| | Section 8 "T | est information": added | | | |
| | Section 9 "P | ackage outline": supersede | ed by minimized packag | e outline drawings | |
| | Section 10 " | Packing information": adde | ed | | |
| | Section 11 " | Soldering": added | | | |
| | Section 13 " | Legal information": updated | d | | |
| PEMB13_PUMB13 v.3 | 20040415 | Product data sheet | - | PEMB13_PUMB13 v.2 | |
| PEMB13_PUMB13 v.2 | 20031211 | Product specification | - | PEMB13 v.1 | |
| PEMB13 v.1 | 20020114 | Preliminary specification | - | - | |
| | | | | | |

13. Legal information

13.1 Data sheet status

| Document status[1][2] | Product status[3] | Definition |
|--------------------------------|-------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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| Product [short] data sheet | Production | This document contains the product specification. |

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- [2] The term 'short data sheet' is explained in section "Definitions"
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PEMB13_PUMB13

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PEMB13; PUMB13

PNP/PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 47 k Ω

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PNP/PNP resistor-equipped transistors; R1 = 4.7 kΩ, R2 = 47 kΩ

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